(5)

PATENT ABSTRACTS OF JAPAN

(11)Publication number : 02-000316
(43)Date of publication of application : 05.01.1990

(51)Int.Cl. H01L 21/302
C30B 33/12
H01L 21/205
H01L 21/86

(21)Application number : 63-091703
(22)Date of filing : 15.04.1988

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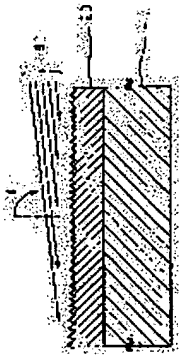
(30)Priority

Priority number : 62145244 ????Priority date : 12.06.1987 ????Priority country : JP
62295379 25.11.1987
JP

(54) SURFACE FLATTENING METHOD AND SOI SUBSTRATE FORMING METHOD USING SAID SURFACE FLATTENING METHOD

(57)Abstract:
PURPOSE: To easily flatten a body surface without contaminating the body surface by rotating the body, and projecting an ion beam onto the surface of the body at an incidence angle of about 85° or more with respect to the normal direction of the surface.
CONSTITUTION: A single crystal spinal film 20 formed by CVD method is laminated on a single crystal silicon substrate 1. While the substrate 1 on which the spinel film 20 is formed is rotated in a horizontal plane, an argon ion beam is projected at an incidence angle of 80° or more with respect to the normal direction of the spinel film 20 surface. Thereby, fine unevenness on the spinel film 20 surface is etched and eliminated, so that the spinel film 20 surface can be flattened without contamination of the spinel film 20 surface or exfoliation of the spinel film 20, as observed in the case of the conventional polishing method.



LEGAL STATUS

[Date of request for examination]

[Date of sending the examiner's decision of rejection]

[Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]

[Date of final disposal for application]

[Patent number]

[Date of registration]

[Number of appeal against examiner's decision of rejection]

[Date of requesting appeal against examiner's decision of rejection]

[Date of extinction of right]